

# PMV160UP

# 20 V, 1.2 A P-channel Trench MOSFET Rev. 2 — 6 December 2011

Product data sheet

### **Product profile**

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- 1.8 V R<sub>DSon</sub> rated
- Very fast switching

Trench MOSFET technology

### 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	-1.2	Α
Static charact	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$		-	170	210	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

### **Pinning information**

**Pinning information** Table 2.

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	3	
3	D	drain	1	G S 017aaa257



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# 3. Ordering information

### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMV160UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

# 4. Marking

### Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PMV160UP	NH%

<sup>[1] % =</sup> placeholder for manufacturing site code

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### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		9 - 9 - 1 - 1				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-1.2	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-0.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \text{ µs}$		-	-4	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	335	mW
			<u>[1]</u>	-	480	mW
		T <sub>sp</sub> = 25 °C		-	2170	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-0.5	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

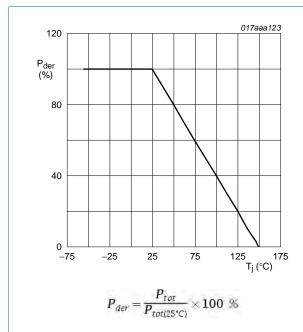
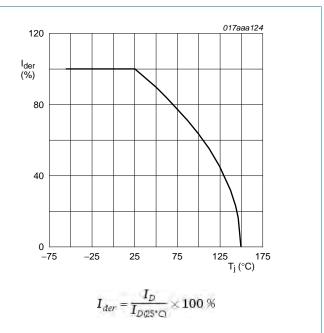
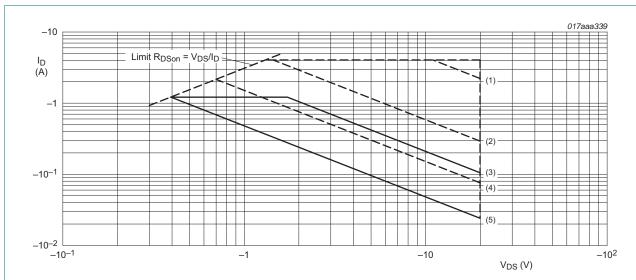


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

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I<sub>DM</sub> = single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	325	374	K/W
	from junction to ambient		[2]	-	227	260	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	50	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

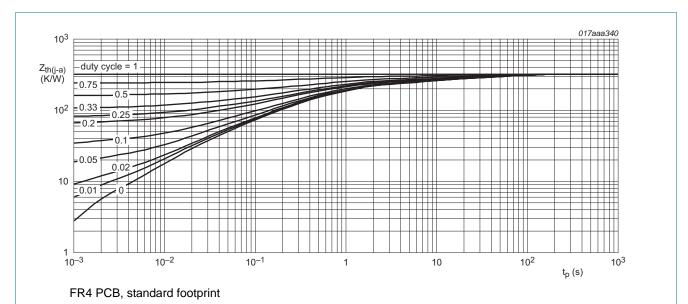
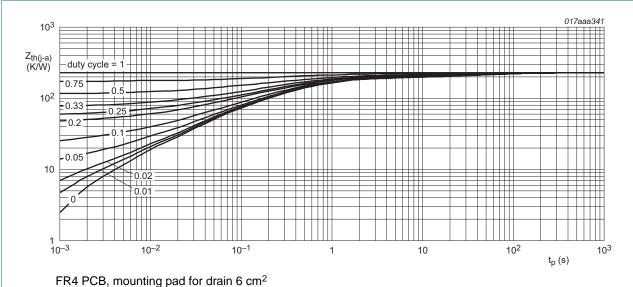


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig 5.

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# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	170	210	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 150 \text{ °C}$	-	265	328	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.1 \text{ A}; T_j = 25 \text{ °C}$	-	210	270	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -0.5 \text{ A}; T_j = 25 \text{ °C}$	-	280	380	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	3.7	-	S
Dynamic (	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	3.3	4	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	1	-	nC
$Q_{GD}$	gate-drain charge		-	0.5	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	365	-	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C	-	42	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	30	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ;	-	7	-	ns
t <sub>r</sub>	rise time	$T_j = 25 ^{\circ}\text{C};  I_D = -1 ^{\circ}\text{A}$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	35	-	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-dr	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -0.5 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

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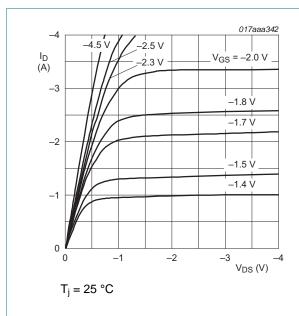
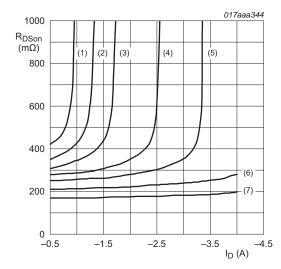


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T<sub>i</sub> = 25 °C

(1)  $V_{GS} = -1.4 \text{ V}$ 

(2)  $V_{GS} = -1.5 \text{ V}$ 

(3)  $V_{GS} = -1.6 \text{ V}$ 

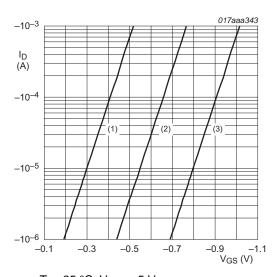
(4)  $V_{GS} = -1.8 \text{ V}$ 

(5)  $V_{GS} = -2.0 \text{ V}$ 

(6)  $V_{GS} = -2.5 \text{ V}$ 

(7)  $V_{GS} = -4.5 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



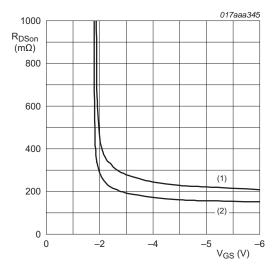
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = -2.5 A$ 

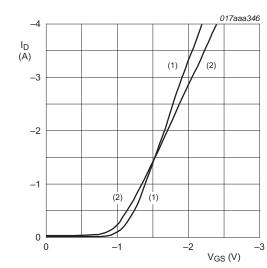
(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

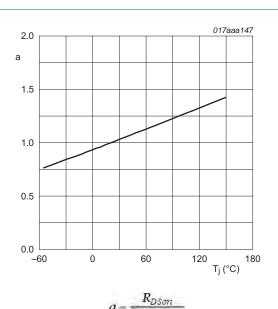
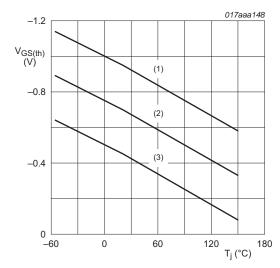


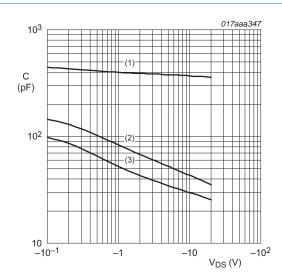
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

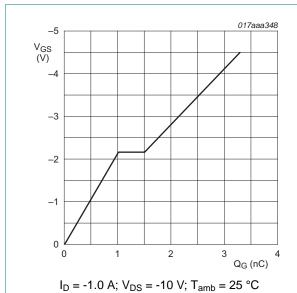


 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)

V<sub>GS</sub>(th)

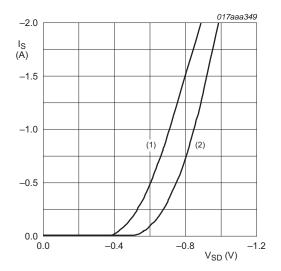
V<sub>GS</sub>

Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>G</sub>(tot)

017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

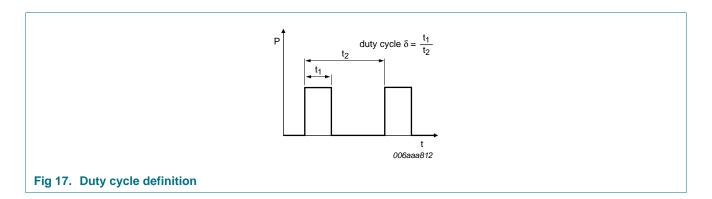
(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

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# 8. Test information



### 20 V, 1.2 A P-channel Trench MOSFET

# 9. Package outline

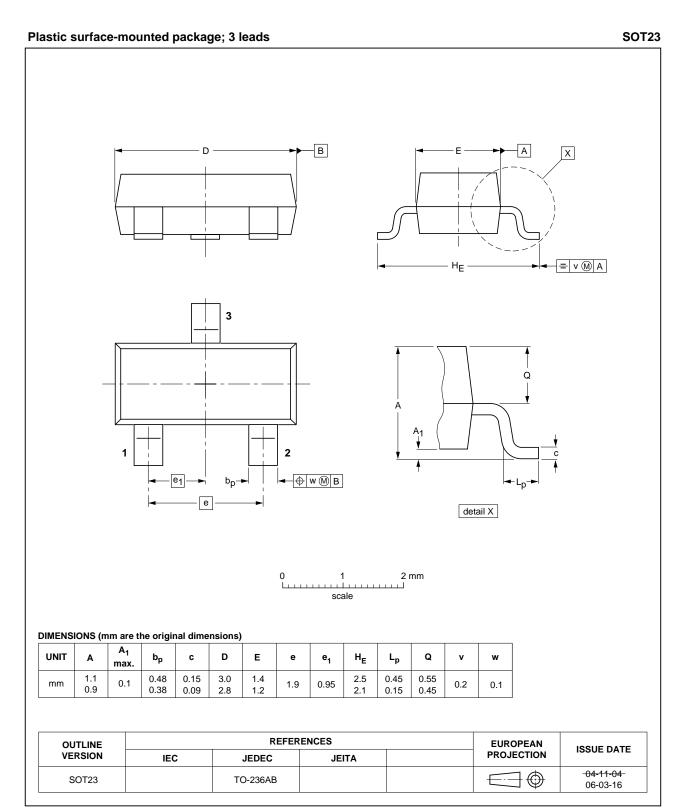
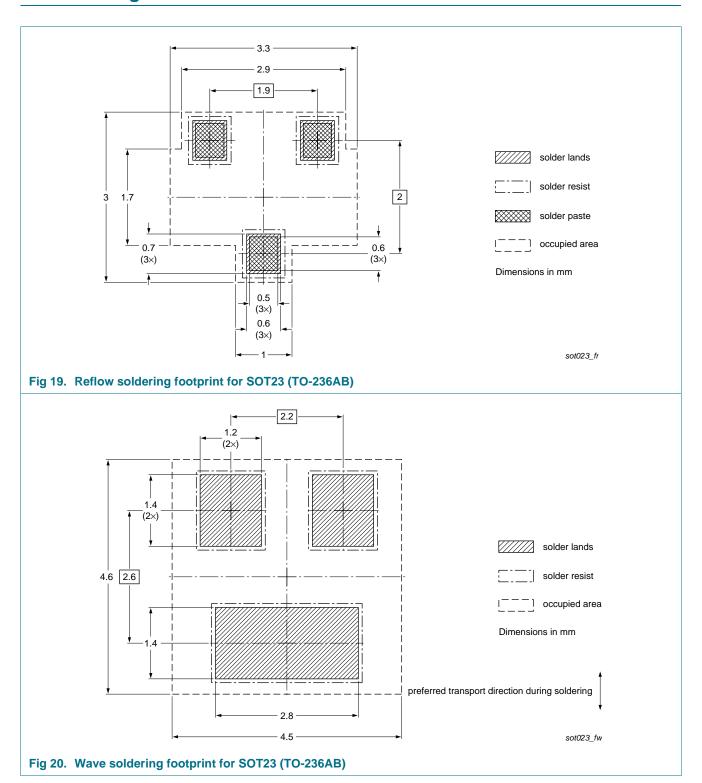


Fig 18. Package outline SOT23 (TO-236AB)

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# 10. Soldering



### 20 V, 1.2 A P-channel Trench MOSFET

# 11. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV160UP v.2	20111206	Product data sheet	-	PMV160UP v.1
Modifications:	<ul> <li>7 "Characteristics"</li> </ul>	: V <sub>GSth</sub> condition is correc	cted	
PMV160UP v.1	20110907	Product data sheet	-	-

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### 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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